TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS210

August 1997

CD74HC4075, CD74HCT4075

High Speed CMOS Logic Triple 3-Input OR Gate

Features

- Buffered Inputs
- Typical Propagation Delay: 8ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}

Description

The Harris CD74HC4075, CD74HCT4075 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 74HCT logic family is functionally pin compatible with the standard 74LS logic family.

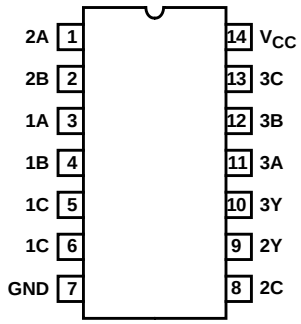
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC4075E	-55 to 125	14 Ld PDIP	E14.3
CD74HC4075E	-55 to 125	14 Ld PDIP	E14.3
CD74HC4075M	-55 to 125	14 Ld SOIC	M14.15
CD74HC4075M	-55 to 125	14 Ld SOIC	M14.15
CD54HC4075H	-55 to 125	Die	
CD54HCT4075H	-55 to 125	Die	
CD54HC4075W	-55 to 125	Wafer	
CD54HCT4075W	-55 to 125	Wafer	

NOTE: When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

Pinout

CD74HC4075, CD74HCT4075
(PDIP, SOIC)
TOP VIEW



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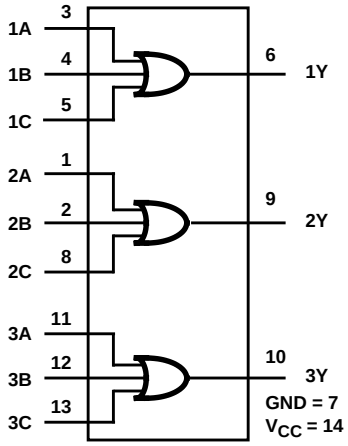
Functional Diagram

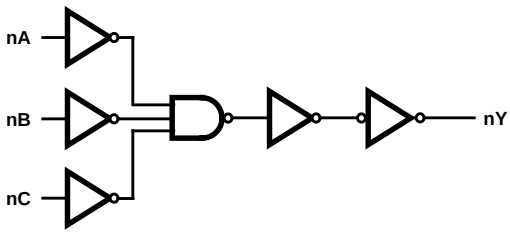


TRUTH TABLE

INPUTS			OUTPUT
nA	nB	nC	nY
L	L	L	L
H	X	X	H
X	H	X	H
X	X	H	H

NOTE: H = High Voltage Level, L = Low Voltage Level, X = Irrelevant

Logic Diagram



Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} or I_{GND} . . . . . ±50mA

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} ($^oC/W$)	θ_{JC} ($^oC/W$)
PDIP Package	100	N/A
SOIC Package	180	N/A

Maximum Junction Temperature (Hermetic Package or Die) . . . 175^oC
Maximum Junction Temperature (Plastic Package) . . . . . 150^oC
Maximum Storage Temperature Range . . . . . -65^oC to 150^oC
Maximum Lead Temperature (Soldering 10s) . . . . . 300^oC
(SOIC - Lead Tips Only)

Operating Conditions

Temperature Range (T_A) . . . . . -55^oC to 125^oC
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS V_I (V)	TEST CONDITIONS I_O (mA)	V_{CC} (V)	25°C MIN	25°C TYP	25°C MAX	-40°C TO 85°C MIN	-40°C TO 85°C MAX	-55°C TO 125°C MIN	-55°C TO 125°C MAX	UNITS
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	2	-	20	-	40	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS V_I (V)	TEST CONDITIONS I_O (mA)	V_{CC} (V)	25°C MIN	25°C TYP	25°C MAX	-40°C TO 85°C MIN	-40°C TO 85°C MAX	-55°C TO 125°C MIN	-55°C TO 125°C MAX	UNITS
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	2	-	20	-	40	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
All	1.6

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g. 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C MIN	25°C TYP	25°C MAX	-40°C TO 85°C MIN	-40°C TO 85°C MAX	-55°C TO 125°C MIN	-55°C TO 125°C MAX	UNITS
HC TYPES											
Propagation Delay, Input to Output (Figure 1)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	100	-	125	-	150	ns
			4.5	-	-	20	-	25	-	30	ns
			6	-	-	17	-	21	-	26	ns
		C_L = 15pF	5	-	8	-	-	-	-	-	ns
Transition Times (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Power Dissipation Capacitance (Notes 2, 3)	C_{PD}	-	5	-	26	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 2)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	24	-	30	-	36	ns
		C_L = 15pF	5	-	9	-	-	-	-	-	ns
Transition Times (Figure 2)	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 2, 3)	C_{PD}	-	5	-	28	-	-	-	-	-	pF

NOTES:

2. C_{PD} is used to determine the dynamic power consumption, per gate.
3. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

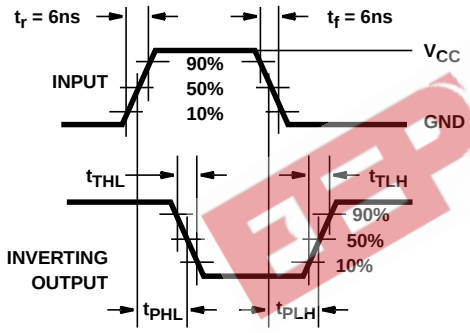


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

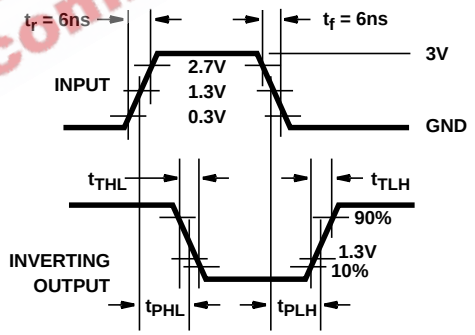


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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